

B1
11 (Amended). A method of manufacturing a semiconductor device, comprising steps of:
forming a semiconductor film;
removing a contaminating impurity from the surface of the semiconductor film; and
forming a gate insulating film in contact with the semiconductor film from the surface of
which the contaminating impurity has been removed.

B2
15 (Amended). A method of manufacturing a semiconductor device, comprising steps of:
forming at least one semiconductor island over a substrate;
spinning the substrate by using a spinning apparatus;
contacting an etching solution to a surface of said semiconductor island and scattering the
etching solution during said spinning, thereby contaminating impurities are removed from the
surface; and then
forming a gate insulating film over said semiconductor island.

B3
23 (Amended). A method of manufacturing a semiconductor device, comprising steps of:
forming gate wirings over a substrate;
spinning the substrate by using a spinning apparatus;
contacting an etching solution to surfaces of said substrate and said gate wirings and
scattering the etching solution during said spinning, thereby contaminating impurities are removed
from the surfaces; and then
forming a gate insulating film and a semiconductor film over said gate wirings.